

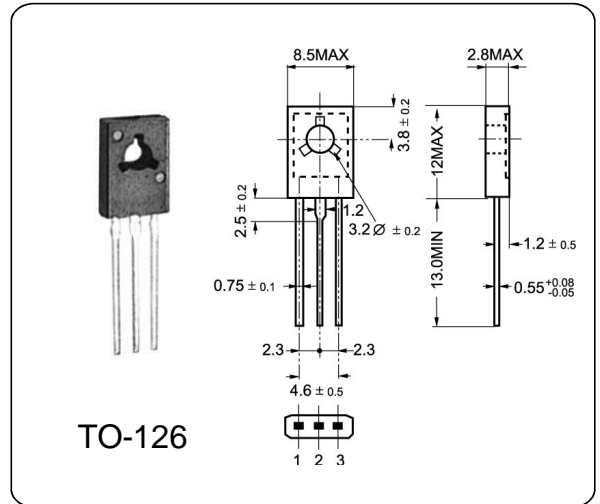


DESCRIPTION

It is intended for use in power amplifier and switching applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	3.0	A
Base Current	I_B	0.3	A
Total Dissipation at	P_{tot}	10	W
Max. Operating Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Collector Cut-off Current	I_{CEO}	$V_{CB}=30V, I_E=0$			0.01	mA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=3V, I_C=0$			0.01	mA
Collector-Emitter Sustaining Voltage	V_{CEO}	$I_C=10mA, I_B=0$	30			V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=2V, I_C=20mA$	30	150		
	$h_{FE(2)}$	$V_{CE}=2V, I_C=1.0A$	60	160	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2A, I_B=200mA$		0.3	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=2A, I_B=200mA$		1.0	2.0	V
Current Gain Bandwidth Product	f_T	$V_{CE}=5V, I_C=100mA$		90		MHz